

GENERAL FEATURES

- $V_{DS} = 50V, I_D = 0.22A$

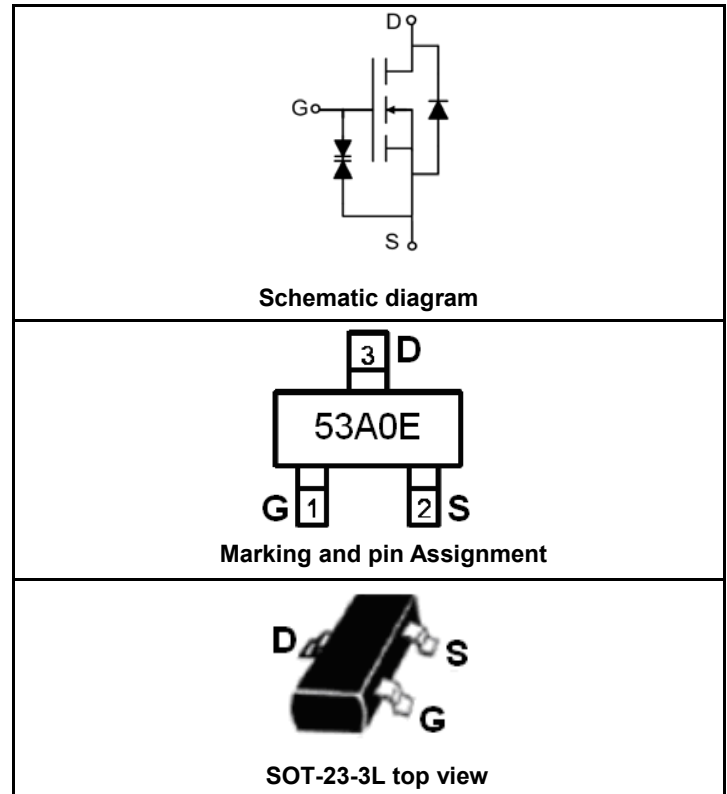
$R_{DS(ON)} < 6\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 3.5\Omega @ V_{GS}=10V$

ESD Rating: 1000V HBM

- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

APPLICATION

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
53A0E	SSF53A0E	SOT-23-3L	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	0.22	A
	$I_D(70^\circ C)$	0.18	
	I_{DM}	0.88	A
Maximum Power Dissipation	P_D	0.36	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=50V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			10	μA
Gate-Source Breakdown Voltage	BV_{GSO}	$V_{DS}=0V, I_G=\pm 250\mu A$	± 20			V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=1mA$	0.5		1.1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.22A$			3.5	Ω
		$V_{GS}=4.5V, I_D=0.22A$			6	
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=0.22A$		0.1		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, F=1.0MHz$		30		PF
Output Capacitance	C_{oss}			15		
Reverse Transfer Capacitance	C_{rss}			6		
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, V_{GS}=10V, R_{GEN}=6\Omega, I_D=0.22A$		2.6		nS
Turn-On Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(off)}$			20		
Turn-Off Fall Time	t_f			6		
Total Gate Charge	Q_g	$V_{DS}=25V, I_D=0.22A, V_{GS}=10V$		1.7	2.4	nC
Gate-Source Charge	Q_{gs}			0.1		
Gate-Drain Charge	Q_{gd}			0.4		
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=0.44A$			1.4	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

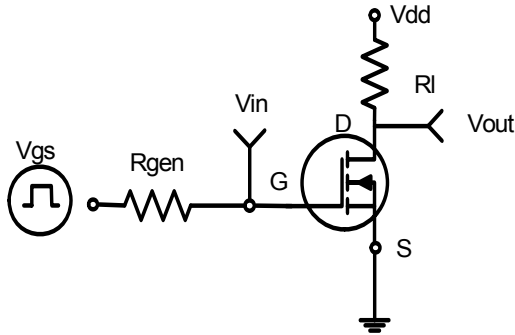


Figure 1: Switching Test Circuit

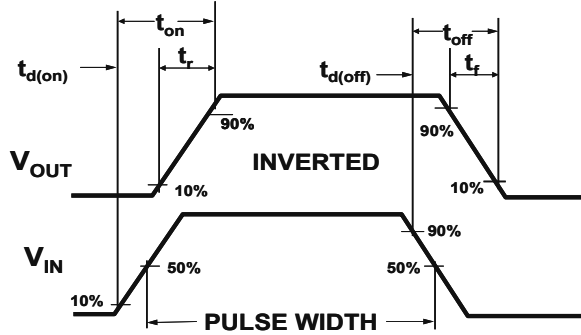


Figure 2: Switching Waveforms

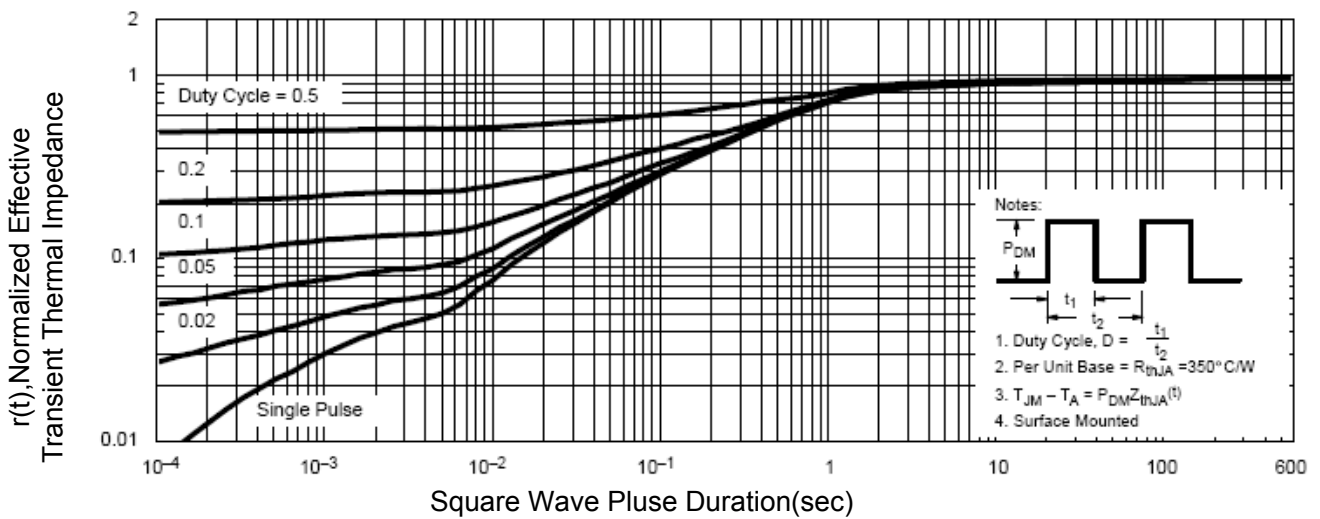
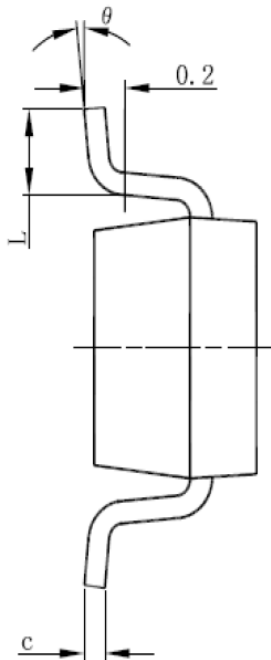
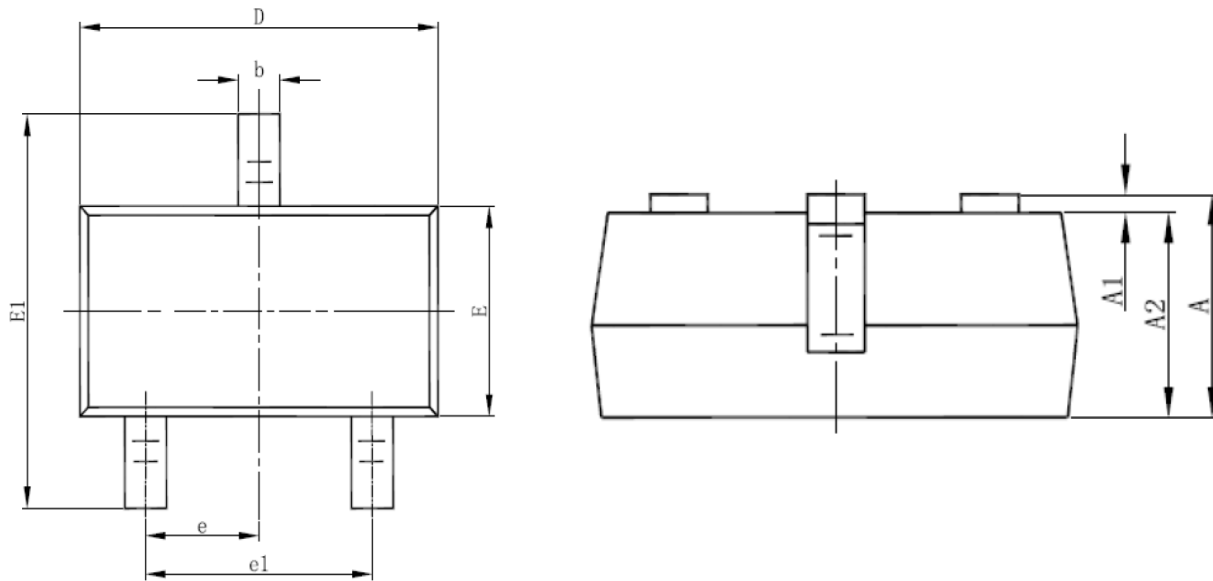


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3L PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.820	3.020
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

NOTES

- All dimensions are in millimeters.
- Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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